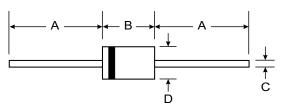


## SILICON SWITCHING DIODE

## **Features**

- High Reliability
- High Conductance
- For General Purpose Switching Applications
- Available in Surface Mount Version (LL4454)



## **Mechanical Data**

• Case: DO-35, Plastic

• Leads: Solderable per MIL-STD-202,

Method 208

Marking: Type NumberPolarity: Cathode BandWeight: 0.13 grams (approx.)

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**Maximum Ratings** @ T<sub>A</sub> = 25°C unless otherwise specified

DO-35							
Dim	Min	Max					
Α	25.40	_					
В	_	4.00					
С	_	0.60					
D	_	2.00					
All Dimensions in mm							

Characteristic	Symbol	1N4454	Unit	
Peak Repetitive Reverse Voltage	$V_{RRM}$			
Working Peak Reverse Voltage	$V_{RWM}$	75	V	
DC Blocking Voltage	$V_{R}$			
Forward Continuous Current (Note 1)	I <sub>FM</sub>	300	mA	
Average Rectified Output Current (Note 1)	l <sub>0</sub>	150	mA	
Non-Repetitive Peak Forward Surge Current @ $t \le 1.0s$ @ $t = 1.0\mu s$	I <sub>FSM</sub>	1.0 2.0	Α	
Power Dissipation (Note 1)	P <sub>d</sub>	400	mW	
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{ hetaJA}$	300	K/W	
Operating and Storage Temperature Range	$T_{j},T_{STG}$	-65 to +175	°C	

## **Electrical Characteristics** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Maximum Forward Voltage Drop	V <sub>FM</sub>	_	_	1.0	V	I <sub>F</sub> = 10mA
Maximum Peak Reverse Current	I <sub>RM</sub>	_	_	100	nA	V <sub>R</sub> = 50V
Junction Capacitance	Cj	_	4.0	_	pF	V <sub>R</sub> = 0V, f = 1.0MHz
Reverse Recovery Time	t <sub>rr</sub>	_	4.0	_	ns	$I_F = I_R = 10 \text{mA},$ $I_{rr} = 0.1 \text{ x } I_R, R_L = 100 \Omega$

Note: 1. Valid provided that leads are kept at ambient temperature.